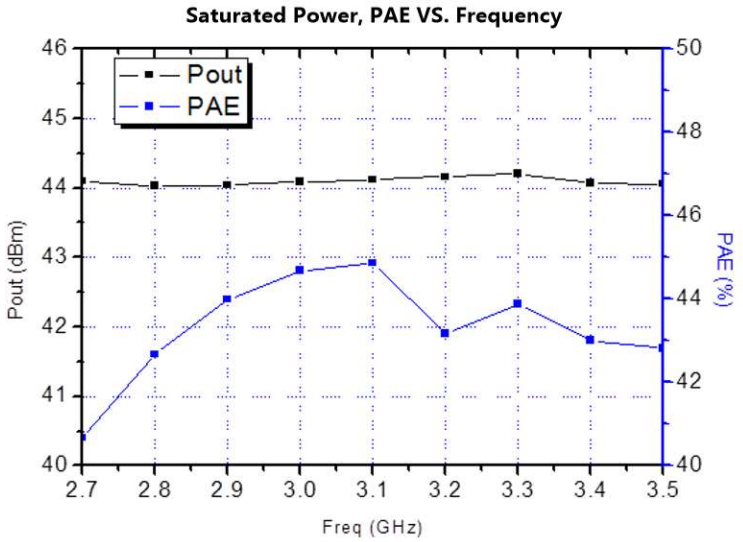
Performance

- Frequency: 2.7-3.5GHz
- Pout: 44dBm@48V
- PAE: 40% (Typ.)
- Small Signal Gain: 30dB
- Bias V_D=48V, V_G=-3.0V (Typ.)
- Size: 18.0*12.9*4.7mm

Electrical Specifications (V_D=48V, V_G=-3V, F: 2.7~3.5GHz, Pulsed 100us, 15% D.C)

Symbol	Parameter	Min	Typical	Max	Unit
G_{SS}	Small Signal Gain @ P_{IN}=0dBm	-	30	-	dB
G	Large Signal Gain @ P_{IN}=18dBm	-	26	-	dB
P_{SAT}	Saturated Power @ P_{IN}=18dBm	-	44	-	dBm
$VSWR_{IN}$	Input VSWR	-	2.6	-	
PAE	Power Added Efficiency @ P_{IN}=18dBm	-	40		%

Test Curves (Large signal)



Absolute Max Ratings (T_A=25℃)

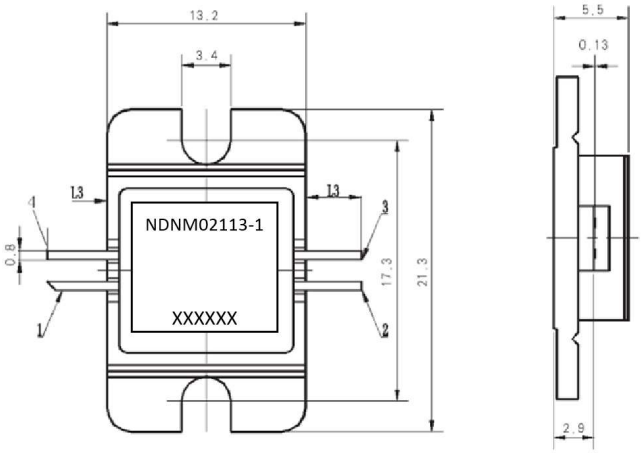
Symbol	Parameter	Value	Remark
Vd	Drain Voltage	60V	
Vg	Gate Voltage	-5V	
Pd	DC Power	600W	
Tch	Channel Temperature	225℃	
Tm	Mounting Temperature	310℃	1min, N_2 protection
Tstg	Storage Temperature	-55~175℃	

Exceeding any one or combination of these limits may cause permanent damage.

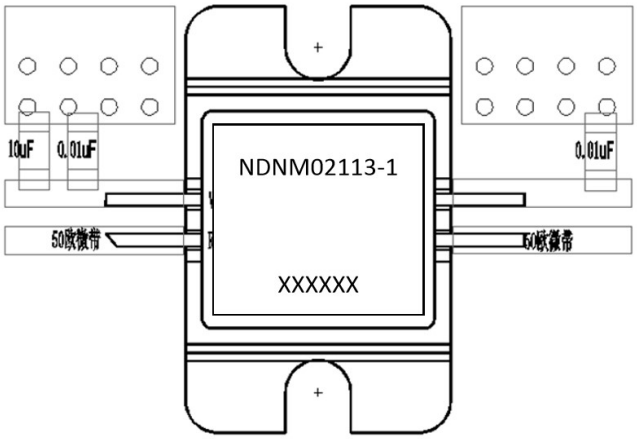
Thermal Information

Parameter	Value	Units
Thermal Resistance (θ_{JC})	2.0	°C/W

Outline Size



Application Circuit



Bias-up Procedure

1 Apply $V_G \approx -3.0V$(typ.)
2 Apply +48V to V_D
3 Apply pulse signal generator
4 Turn on RF supply

Bias-down Procedure

1 Turn off RF supply
2 Turn off pulse signal generator
3 Turn off V_D supply
4 Turn off V_G supply